

2N5945

NPN SILICON RF POWER TRANSISTOR

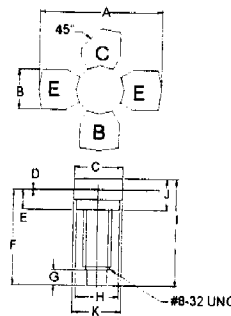
FEATURES:

- Common Emitter
- $P_G = 9.0$ dB at 2.0 W/470 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.8 A
V_{CB0}	36 V
V_{CEO}	16 V
V_{EBO}	4.0 V
P_{DISS}	15 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	11.6 $^\circ\text{C}/\text{W}$

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM <small>(inches / mm)</small>	MAXIMUM <small>(inches / mm)</small>
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F		.572 / 14.53
G		.130 / 3.30
H	.245 / 6.22	.265 / 6.48
I		.640 / 16.26
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	16			V
BV_{CES}	$I_C = 100$ mA	36			V
BV_{EBO}	$I_E = 2.0$ mA	4.0			V
I_{CB0}	$V_{CB} = 15$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	20	---	---	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz	---	18	25	pF
P_G	$V_{CC} = 12.5$ V $P_{OUT} = 4.0$ W $f = 470$ MHz	9.0	10		dB
η_c		60			%

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